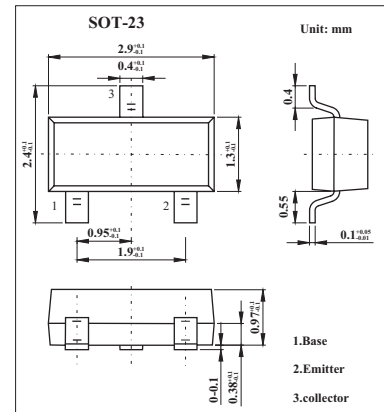


## Silicon PNP Epitaxial

## 2SA1484

## ■ Features

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector to base voltage	$V_{CB0}$	-90	V
Collector to emitter voltage	$V_{CE0}$	-90	V
Emitter to base voltage	$V_{EB0}$	-5	V
Collector current	$I_c$	-100	mA
Collector power dissipation	$P_c$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_c = -10 \mu\text{A}, I_E = 0$	-90			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_c = -1 \text{ mA}, R_{BE} = \infty$	-90			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -70 \text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -2 \text{ V}, I_c = 0$			-0.1	$\mu\text{A}$
DC current transfer ratio	$h_{FE}$	$V_{CE} = -12 \text{ V}, I_c = -2 \text{ mA} (*)$	250		800	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_c = -10 \text{ mA}, I_B = -1 \text{ mA} (*)$			-0.15	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA} (*)$			-1	V

\* Pulse test.

■  $h_{FE}$  Classification

Marking	IRD	IRE
$h_{FE}$	250~500	400~800